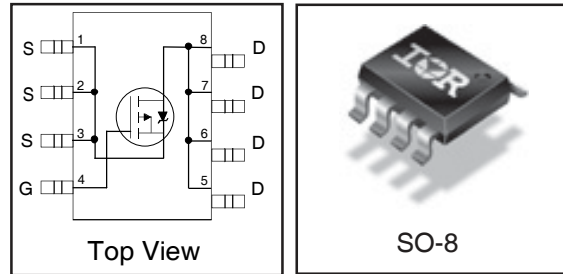


HEXFET® Power MOSFET

$V_{DS}$	<b>-12</b>	<b>V</b>
$R_{DS(on) \max}$ (@ $V_{GS} = -4.5V$ )	<b>7</b>	<b>m<math>\Omega</math></b>
$R_{DS(on) \max}$ (@ $V_{GS} = -2.5V$ )	<b>9</b>	
$R_{DS(on) \max}$ (@ $V_{GS} = -1.8V$ )	<b>13</b>	
$Q_g$ (typical)	<b>91</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>-16</b>	<b>A</b>



**Features**

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



**Benefits**

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7410PbF-1	SO-8	Tape and Reel	4000	IRF7410TRPbF-1

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-12	V
$I_D$ @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ -4.5V	-16	A
$I_D$ @ $T_A = 70^\circ C$	Continuous Drain Current, $V_{GS}$ @ -4.5V	-13	
$I_{DM}$	Pulsed Drain Current ①	-65	
$P_D$ @ $T_A = 25^\circ C$	Power Dissipation ③	2.5	W
$P_D$ @ $T_A = 70^\circ C$	Power Dissipation ③	1.6	
	Linear Derating Factor	20	mW/°C
$V_{GS}$	Gate-to-Source Voltage	±8	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to +150	°C

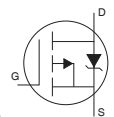
**Thermal Resistance**

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	50	°C/W

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

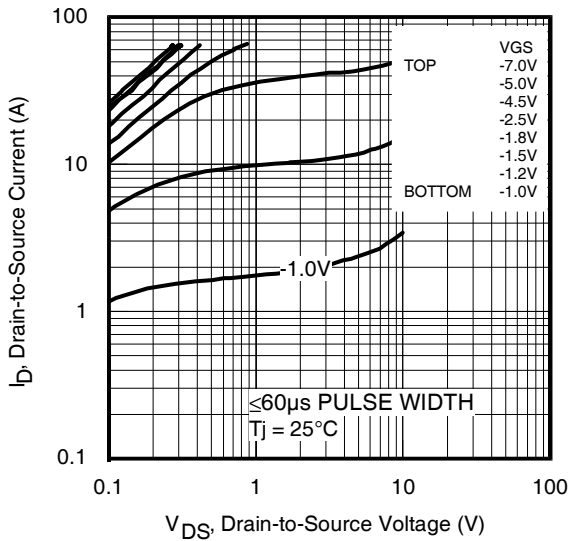
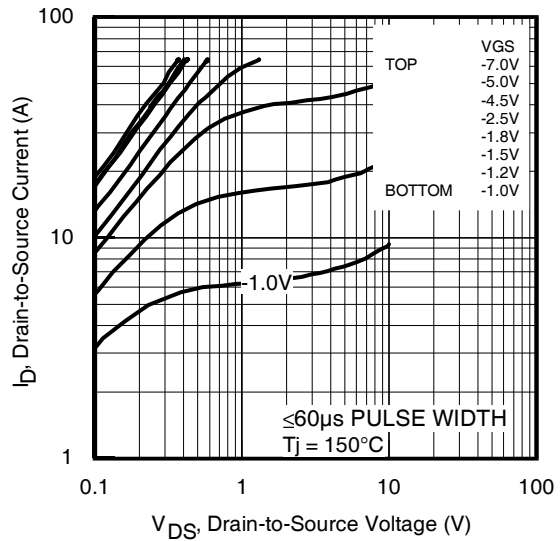
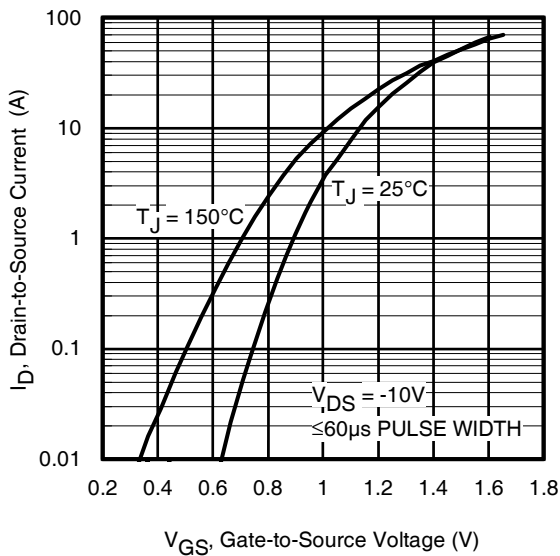
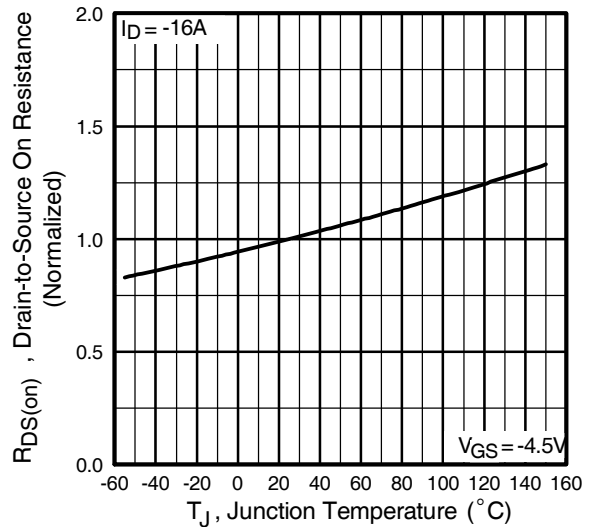
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-12	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.006	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	7	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -16A ②
		—	—	9		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -13.6A ②
		—	—	13		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -11.5A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	-0.4	—	-0.9	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	—	-3.09	—	mV/°C	
g <sub>fs</sub>	Forward Transconductance	55	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -16A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -9.6V, V <sub>GS</sub> = 0V
		—	—	-25		V <sub>DS</sub> = -9.6V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -8V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 8V
Q <sub>g</sub>	Total Gate Charge	—	91	—	nC	I <sub>D</sub> = -16A
Q <sub>gs</sub>	Gate-to-Source Charge	—	18	—		V <sub>DS</sub> = -9.6V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	25	—		V <sub>GS</sub> = -4.5V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	13	20	ns	V <sub>DD</sub> = -6V V <sub>GS</sub> = -4.5V
t <sub>r</sub>	Rise Time	—	12	18		I <sub>D</sub> = -1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	271	407		R <sub>D</sub> = 6Ω
t <sub>f</sub>	Fall Time	—	200	300		R <sub>G</sub> = 6Ω ②
C <sub>iss</sub>	Input Capacitance	—	8676	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	2344	—		V <sub>DS</sub> = -10V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	1604	—		f = 1.0 MHz

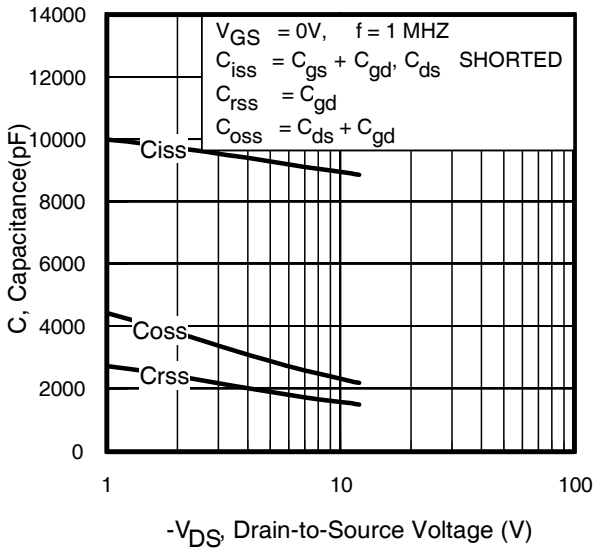
**Source-Drain Ratings and Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-65		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -2.5A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	97	145	ns	T <sub>J</sub> = 25°C I <sub>F</sub> = -2.5A
Q <sub>rr</sub>	Reverse Recovery Charge	—	134	201	μC	di/dt = -100A/μs ②

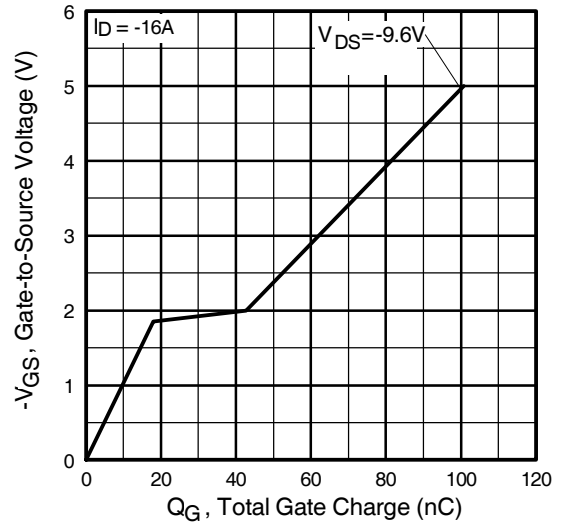
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ③ Surface mounted on 1 in square Cu board, t ≤ 10sec.

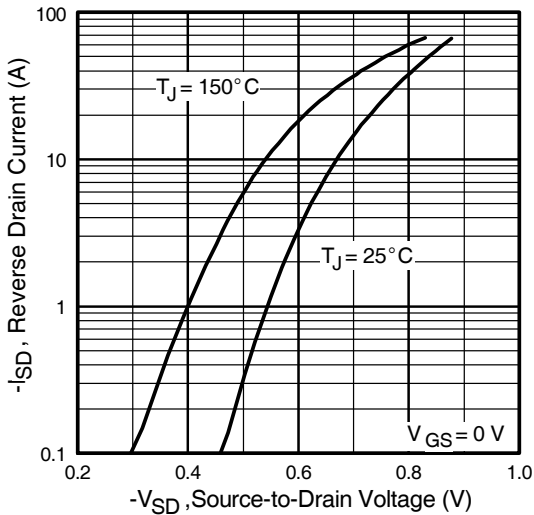

**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance Vs. Temperature**



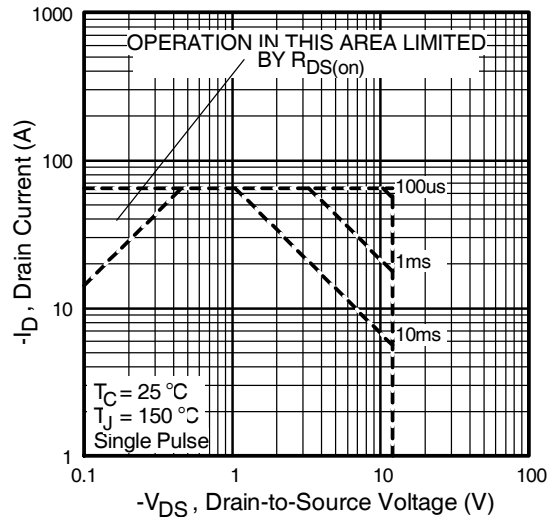
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

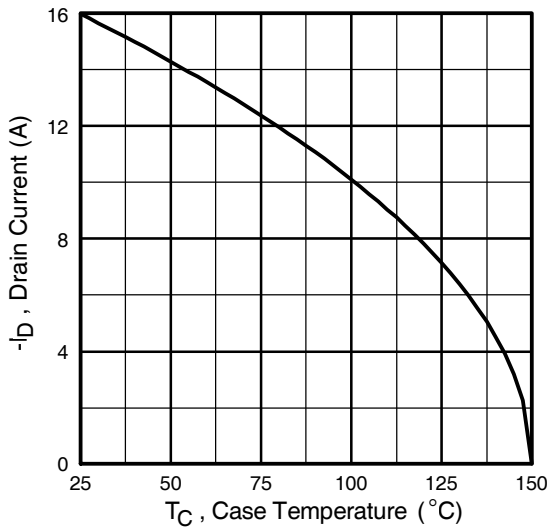


Fig 9. Maximum Drain Current Vs. Case Temperature

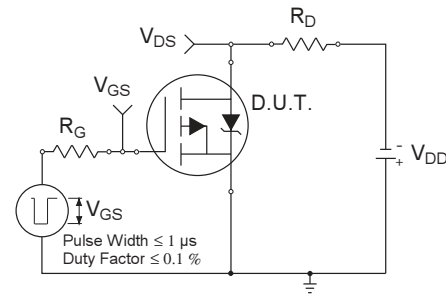


Fig 10a. Switching Time Test Circuit

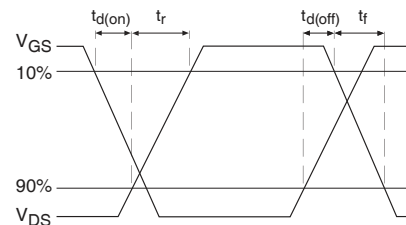


Fig 10b. Switching Time Waveforms

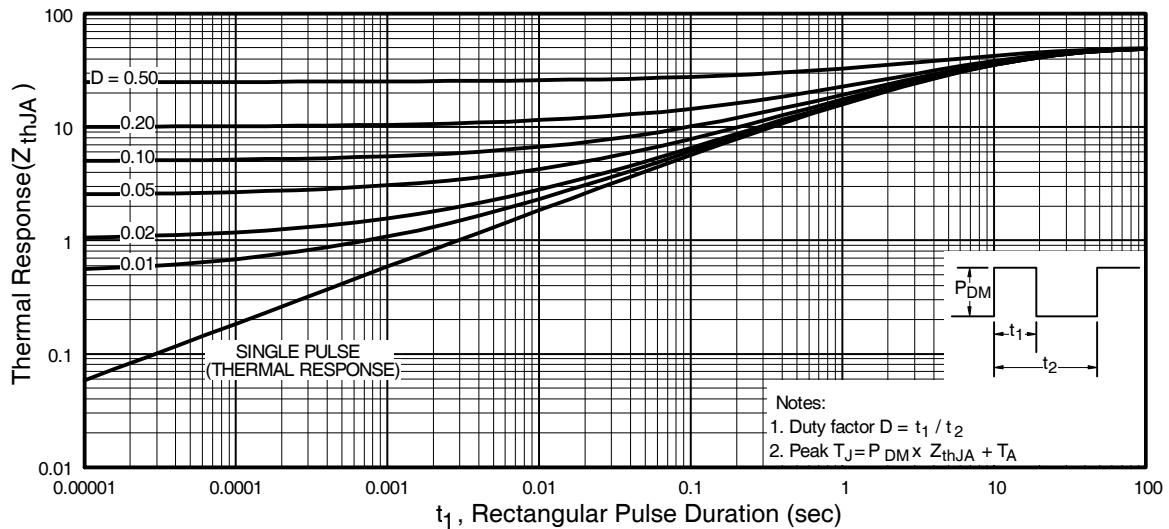
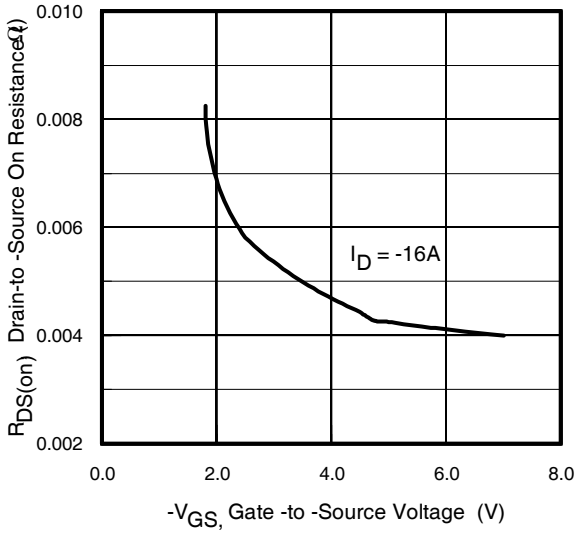
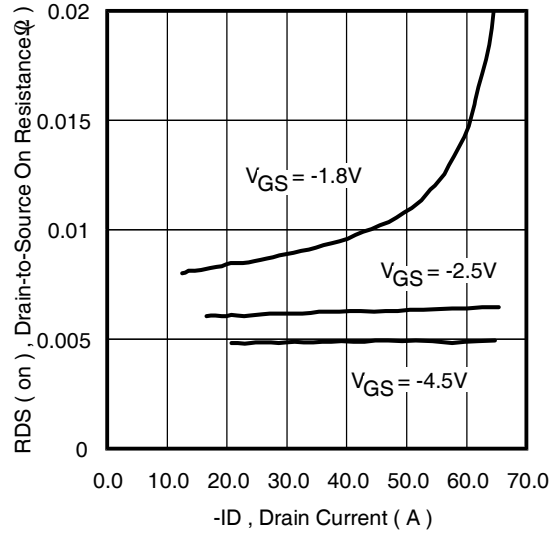


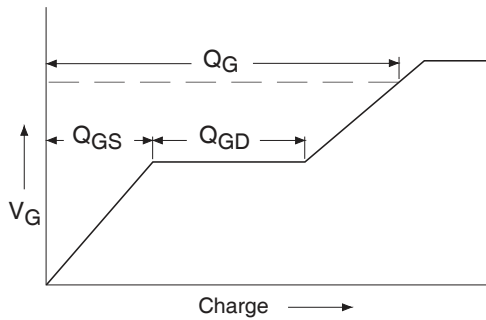
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



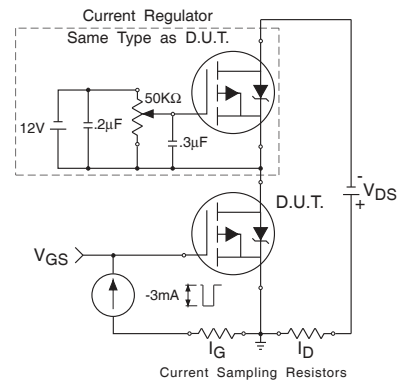
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



**Fig 13.** Typical On-Resistance Vs. Drain Current



**Fig 14a.** Basic Gate Charge Waveform



**Fig 14b.** Gate Charge Test Circuit

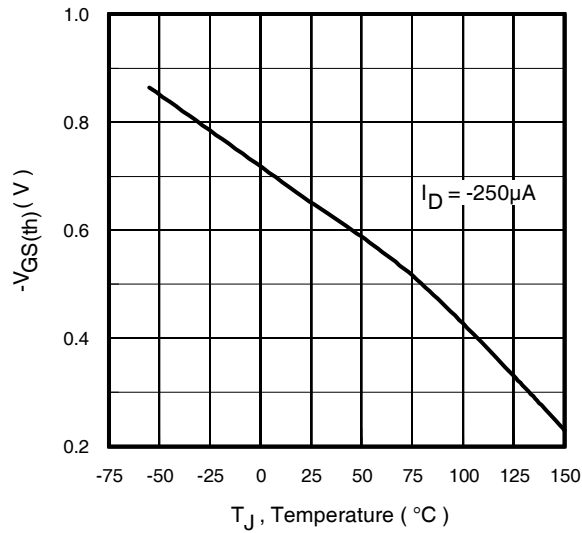


Fig 15. Typical  $V_{GS(th)}$  Vs. Junction Temperature

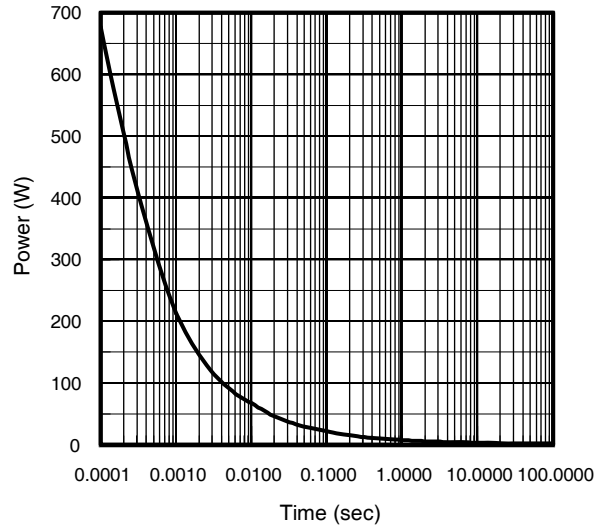
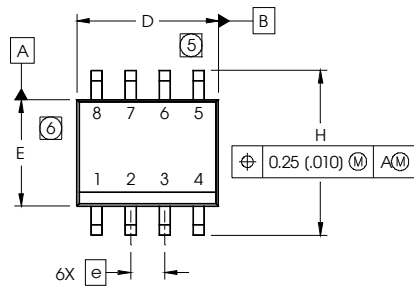


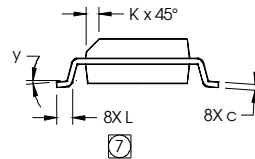
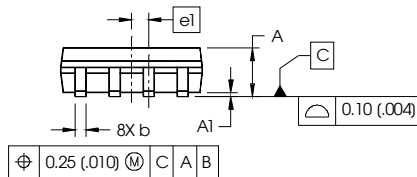
Fig 16. Typical Power Vs. Time

## SO-8 Package Outline (MOSFET & Fetky)

Dimensions are shown in millimeters (inches)

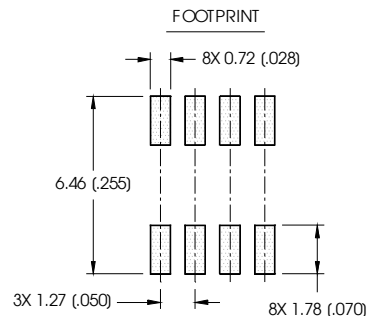


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



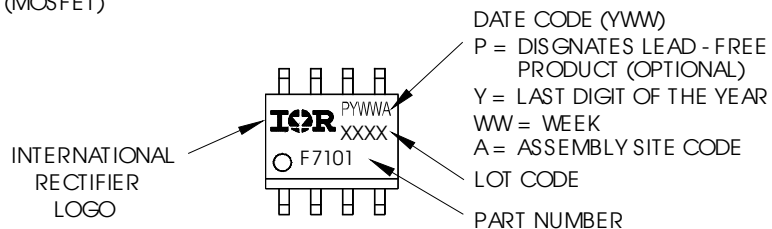
**NOTES:**

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



## SO-8 Part Marking Information

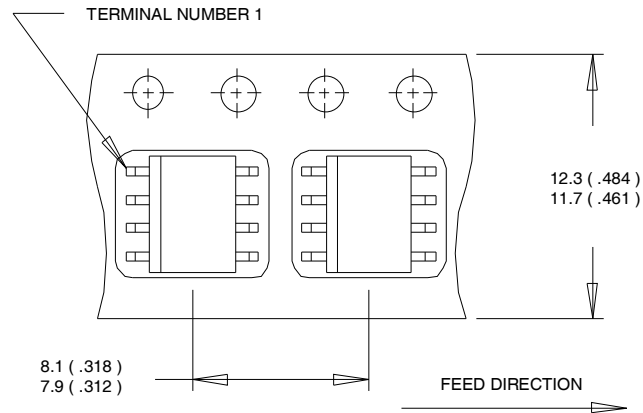
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



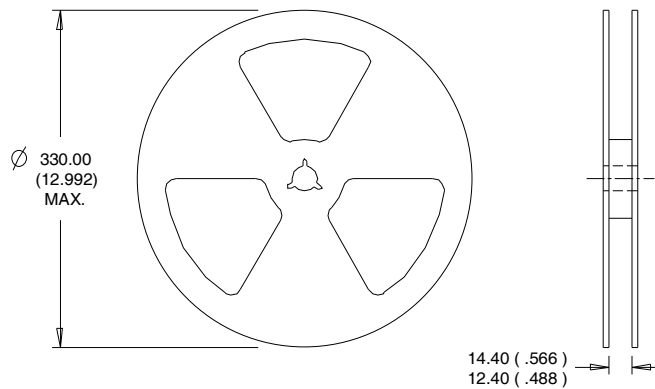
Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



### SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**Qualification information<sup>†</sup>**

Qualification level	Industrial (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

<sup>††</sup> Applicable version of JEDEC standard at the time of product release

**Revision History**

Date	Comments
10/16/2014	<ul style="list-style-type: none"> <li>Corrected part number from "IRF7410PbF-1" to "IRF7410TRPbF-1" -all pages</li> <li>Removed the "IRF7410PbF-1" bulk part number from ordering information on page1</li> </ul>